

REMARKS

Claims 14-27 have been examined. Claims 14 and 22-27 remain in the Application. Claims 1-13, and 15-21 are cancelled. The figures are objected to under 37 C.F.R. § 1.83(a). Claims 14, and 22-24 are rejected under 35 U.S.C. § 112, first paragraph. Claim 14 is amended. Claims 14, 20, and 22 are rejected under 35 U.S.C. § 102.

A. Drawings

Figures 1 and 2 are amended in red ink. Figures 7 and 12 support claims 24-27. Withdrawal of the objection under 37 C.F.R. § 1.83(a) is requested.

B. 35 U.S.C. § 112, First Paragraph: Rejection of Claims 14 and 23-27

Claims 14, 20-21, and 23-27 are rejected under 35 U.S.C. § 112, second paragraph, as indefinite. Claims 20-21 are cancelled. Applicant amended claim 14 to address the specific concerns raised by the Examiner. Withdrawal of the rejection to claim 14 under 35 U.S.C. § 112, second paragraph is respectfully requested. Since claims 23-27 depend directly or indirectly from claim 14, claims 23-27 contain at least the limitations of claim 14. Accordingly, claims 23-27 are sufficiently definite.

C. 35 U.S.C. § 112, Second Paragraph: Rejection of Claims 14 and 23-27

Claims 14, 20-21, and 23-27 are rejected under 35 U.S.C. § 112, Second Paragraph. Claims 20-21 are cancelled. The United States Patent and Trademark Office (USPTO) asserts that claim 14 relates to a "final structure" and that the "damaged surface" is an intermediate step. Office Action dated January 18, 2001, p. 3. Applicant believes that the apparatus is properly claimed with respect to the damaged surface and requests that the USPTO withdraw its rejection.

The USPTO asserts that a structure such as the device that removes the damaged surface must be introduced before the “means clause” as explained by the Examiner to the undersigned on July 17, 2001. Applicant disagrees and requests further support for the USPTO’s assertion.

D. 35 U.S.C. § 102(b): Rejection of Claims 14, 20, and 22

The USPTO rejects claims 14, 20, and 22 under 35 U.S.C. § 102(b) as anticipated by pages 2-3 of the Application. Claim 20 is cancelled.

Horiba does not anticipate Claim 14. Claim 14 relates to an apparatus that includes “a first substrate with a semiconductor film formed thereon; wherein a bond between said semiconductor film and said first substrate is weakened by a hydrogen ion implanted damaged surface, said semiconductor film is demarcated from a rest of said first substrate by the hydrogen ion implanted damaged surface.” Claim 14 of the marked-up claims, lines 3-6.

Horiba relates to low resistance ground wiring in a semiconductor device. More specifically, *Horiba* relates to fabricating a semiconductor device that includes a first insulating film formed partially on the semiconductor substrate. Gate electrodes are formed on the first insulating film. *Horiba*, col. 4, lines 15-16. A diffusion layer is then formed at a surface of the semiconductor substrate around the gate electrodes. *Horiba*, col. 4, lines 20-21. An insulating sidewall film is formed around a sidewall of the gate electrodes. *Horiba*, col. 4, lines 22-23. A third insulating film is partially covering the semiconductor substrate, the insulating sidewall film, and the gate electrodes so that the diffusion layer, a part of the gate electrodes, and a top edge of the insulating sidewall film are exposed. *Horiba*, col. 4,

lines 23-27. A second conductive film covers the third insulating film, the exposed part of the gate electrodes, the exposed top edge of the insulating sidewall film and the semiconductor substrate. *Horiba*, col. 4, lines 27-31. A third conductive film covers the second conductive film. *Horiba*, lines 1-32. A fourth insulating film has a planarized top surface at such a level that a top surface of the third conductive film is exposed. *Horiba*, lines 32-33. A fourth conductive film bridging over the top surface of the third conductive film. *Horiba*, lines 33-35. The fourth conductive film, the fourth insulating film, the third conductive film and the second conductive film cooperate with one another to form a ground wiring layer.” *Horiba*, col. 4, lines 35-38. Nowhere in *Horiba* does it disclose “a first substrate with a semiconductor film formed thereon; wherein a bond between said semiconductor film and said first substrate is weakened by a hydrogen ion implanted damaged surface, said semiconductor film is demarcated from a rest of said first substrate by the hydrogen ion implanted damaged surface” as in claim 14 of the marked-up claims, lines 3-6. Applicant respectfully requests withdrawal of the rejection under 35 U.S.C. § 102(b) to claim 14. Since claim 22 depends from claim 14, claim 22 has at least the limitations of claim 14. Claim 22, therefore, is also not anticipated by *Horiba* for at least the reasons that claim 14 is not anticipated by *Horiba*.

For the above-stated reasons, Applicant asserts that claims 14 and 22 are not anticipated by *Horiba*. Applicant respectfully requests that the Examiner withdraw the rejection to claims 14 and 22 under 35 U.S.C. § 102(b).

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE".

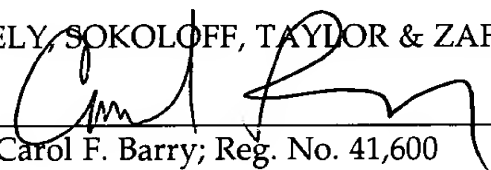
CONCLUSION

In view of the foregoing, it is believed that all claims now pending are now in condition for allowance and such action is earnestly solicited at the earliest possible date. If there are any fees due in connection with the filing of this response, please charge those fees to our Deposit Account No. 02-2666. If a telephone interview would expedite the prosecution of this Application, the Examiner is invited to contact the undersigned at (310) 207-3800.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

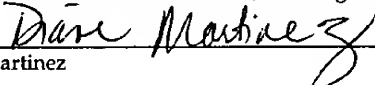
Dated: July 18, 2001

By: 
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CERTIFICATE OF MAILING:

I hereby certify that this correspondence is being deposited as Express Mail with the United States Postal Service in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on July 18, 2001.


Diane Martinez

July 18, 2001

Attachment: VERSION WITH MARKINGS TO SHOW CHANGES MADE

VERSION WITH MARKINGS TO SHOW CHANGES MADE
IN THE CLAIMS

Claims 20-21 are cancelled and claim 14 is amended as follows:

- 1 14. (Three Times Amended) An apparatus comprising:
- 2 a first substrate with a semiconductor film formed thereon;
- 3 wherein a bond between said semiconductor film and said first substrate is
- 4 weakened by a hydrogen ion implanted damaged surface, said semiconductor film is
- 5 demarcated from a rest of said first substrate by [a] the hydrogen ion implanted
- 6 damaged surface.

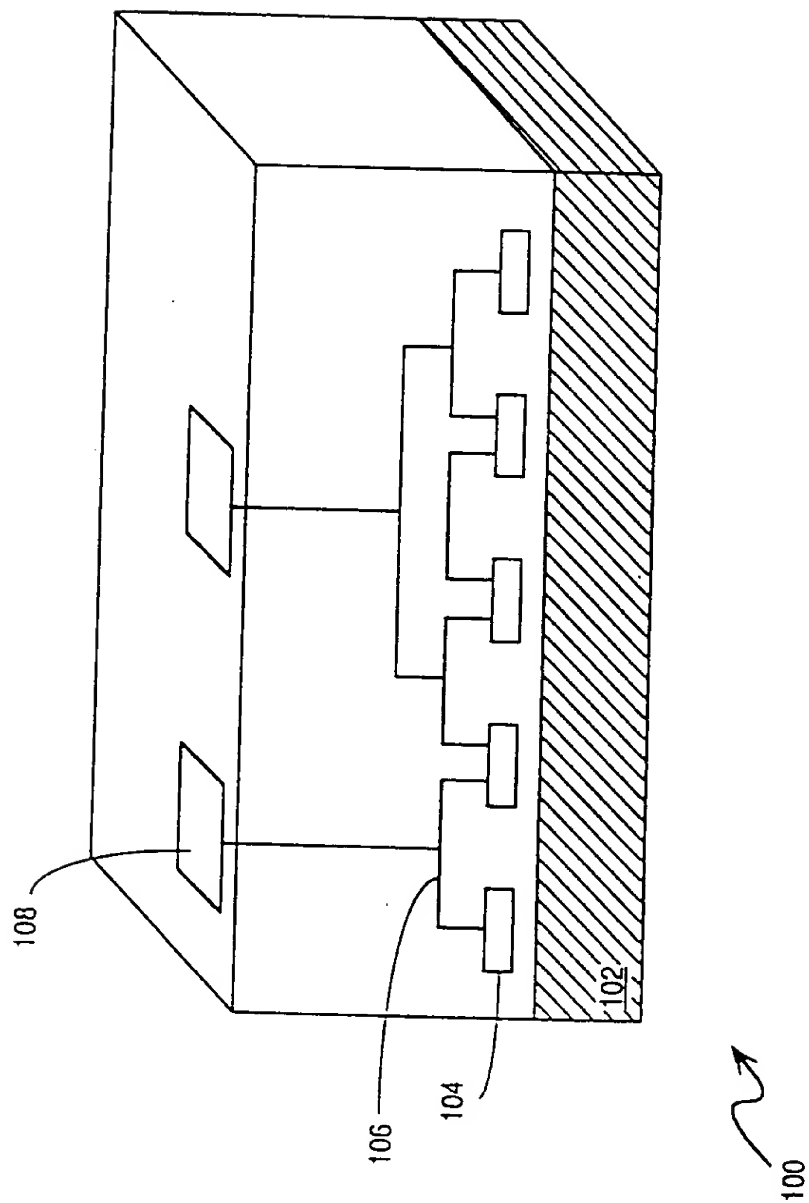


Fig. 1

(PRIOR ART)

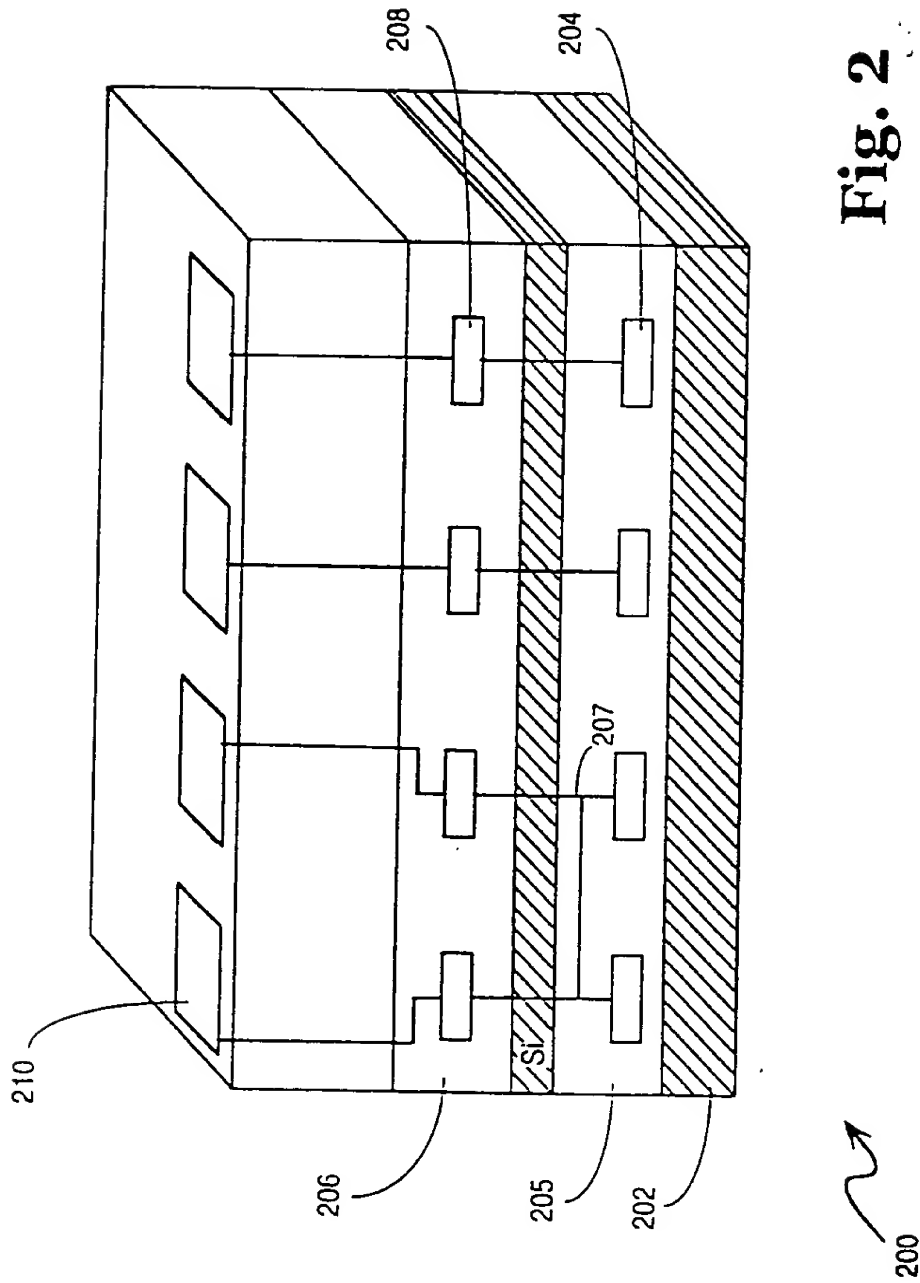


Fig. 2

(PRIOR ART)